

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-102418

(43)Date of publication of application : 23.04.1993

(51)Int.Cl.

H01L 27/108

H01L 21/318

H01L 27/04

(21)Application number : 03-281881

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(22)Date of filing : 03.10.1991

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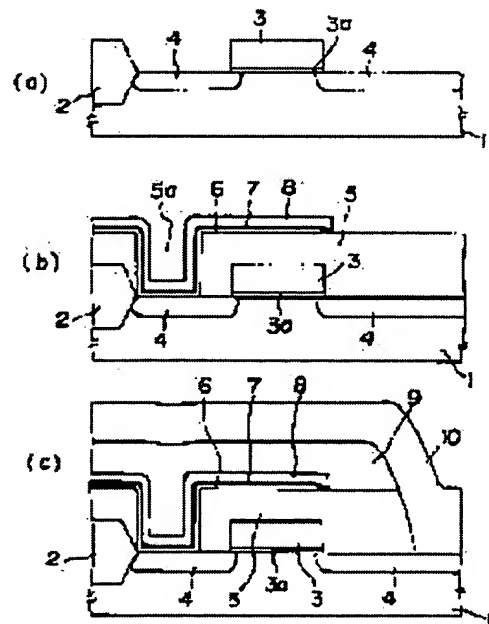
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To provide a manufacturing method of a semiconductor device which enables easy formation of an extremely thin capacitor insulating film of a low defective density and a low leak current and wherein an increase of a cell capacity can be expected.

CONSTITUTION: After a gate electrode 3 and a source/drain 4 are formed on a semiconductor substrate 1, an SiO₂ film 5 is formed all over and a cell contact 5a is formed. Then, after a storage electrode 6 and a silicon nitride film 7 which becomes a capacitor insulating film are formed one by one and annealed at a high temperature, a surface of the silicon nitride film is oxidized in water vapor atmosphere and a cell plate electrode 8 is formed on an upper surface thereof.

Thereafter, a BPSG 9 is formed all over and an aluminum 10 is formed on an upper surface thereof.



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[Date of request for examination]